FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT	MMB DOCKET NO. 1890-0079	APPLICATION NO.: 10/826,921		
IPE 45	APPLICANT(S): Taddiken			
IN 12 THE BE	FILING DATE: April 16, 2004	GROUP ART UNIT: 2811		
PTU				

•			U.S.	PATENT DOCUMENTS				
EXAMINER IŅITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE	
	AA							
	AB						_	
•	AC							
	AD		$\overline{}$					
	AE							
	AF							
	AG							
	AH							
	Al							
	AJ							
	AK							
		<u> </u>				<u> </u>	<u> </u>	
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
	AL						Yes	
						<u> </u>	No	
	AM		+				Yes No	
	AN						Yes No	
	AO						Yes	
	1.2						No	
	AP						Yes	
		O	HER (Including	Author, Title, Date, Pertine	nt Pages, etc.)	<u> </u>		
	AQ					klund, "Output P	ower Characteristics	
		of High Vo	Gebara, Edward, Niklas Rorsman, Jörgen Olsson, Herbert Zirath, Klas Håkan Eklund, "Output Power Characteristics of High Voltage LDMOS Transistors," Proceedings of the 5 th Symposium on Gigahertz Electronics, Goeteborg Sweden, March 2000, pages 75-78, (4 pages).					
D	AR	Conduction	Disney, D. R., A. K. Paul, M. Darwish, R. Basecki, V. Rumennik, "A New 800V Lateral MOSFET With Dual Conduction Paths," Proceedings of the 13 th International Symposium on Power Semiconductor Devices & ICs, Osaka, Japan, June 2001, pages 399-402, (4 pages).					
2	AS		Cai, Jun, Changhong Ren, N. Balasubramanian, Johnny K. O. Sin, "A Novel High Performance Stacked LDD RF LDMOSFET," IEEE Electron Device Letters, Vol. 22, No. 5, May 2001, (3 pages).					
EXAMINER					DATEC	CONSIDERED 2/6/00		
EXAMINER:	Initial if re	ference considered, idered. Include cop	whether or not city	ation is in conformance with next communication to App	MPEP 609. Draw lir	ne through citation	n if not in	

	MMB DOCKET NO. 1890-0079	APPLICATION NO.: 10/826,921
FORM PTO-1449		
INFORMATION DISCLOSURE STATEMENT		
•	APPLICANT(S): Taddiken	
··	FILING DATE: April 16, 2004	GROUP ART UNIT: 2811
•		2815
		,, <u></u>

			U	.S. PATENT DOCUMENTS			
EXAMINER NITIAL		DOCUME NUMBER		NAME	CLASS	SUB-CLASS	FILING DATE
	ВА						
	BB						
	ВС						
	BD						
	BE						
	BF						
	BG						
	ВН						
	BI						
	BJ						
	ВК						
EXAMINER NITIAL		DOCUME NUMBER	l l	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
	BL	<u> </u>					Yes
							No
	ВМ						Ye:
	BN	 					Ye
	DIN						No.
	ВО						Ye
							N
	BP						Yes
					<u> </u>		No
		, , , , , , , , , , , , , , , , , , , 		ng Author, Title, Date, Pertin		······································	
	BQ			J. Olsson, F. Masszi and K. H andard CMOS Process," IEEE			-Voltage Giga-He
/	BR	2					
	BS	2					
	_		Norman.			CONSIDERED	,